



ISSI Pseudo SRAM/CellularRAM™

ISSI has an extensive family of Pseudo SRAM (PSRAM)/CellularRAM™ to offer designers an option of the best of both DRAM and SRAM features. The PSRAM/CellularRAM™ has a SRAM-like architecture. Unlike DRAM, there is a hidden refresh feature which does not require physical refresh. The CellularRAM™ is designed in accordance to the CellularRAM™ standards and is available in CRAM 1.5 and CRAM 2.0.

This family of products offers fast access, asynchronous, page and burst functions for different application requirements. The products support low voltage which reduces over all power consumption. These products are available in commercial, industrial and automotive operating temperature range, which is suitable to support applications in these markets.

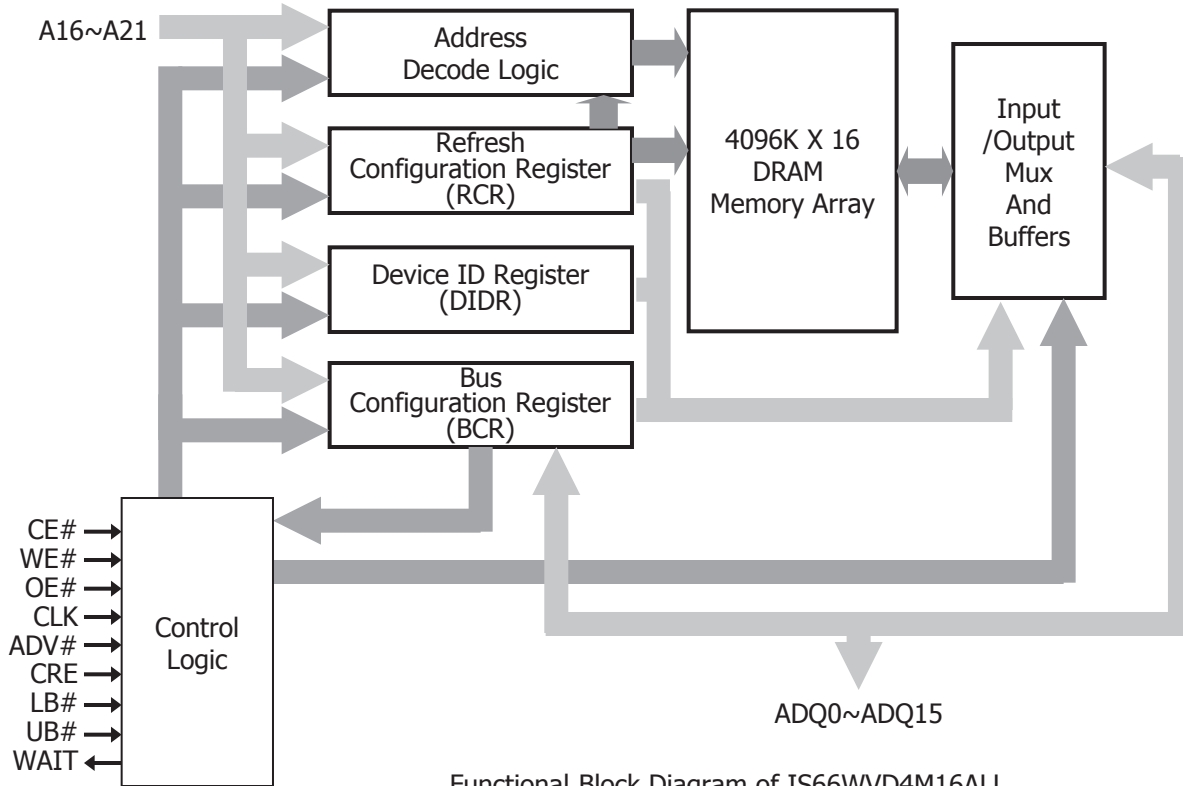
| Density | Org | Product Number | Vcc | Speed (ns) | Pkg(Pins) | Status | Description |
|---------|---------|-----------------|-----------|------------|--------------------|------------|-----------------|
| 8M | 512Kx16 | IS66WV51216DALL | 1.7-1.95V | 70 | TSOP[44], mBGA[48] | Production | Standard Asynch |
| | 512Kx16 | IS66WV51216DBLL | 2.5-3.6V | 55,70 | TSOP[44], mBGA[48] | Production | Standard Asynch |
| 16M | 1MX16 | IS66WV1M16DALL | 1.7-1.95V | 70 | mBGA[48] | Production | Standard Asynch |
| | 1MX16 | IS66WV1M16DBLL | 2.5-3.6V | 55,70 | mBGA[48] | Production | Standard Asynch |
| | 1MX16 | IS66WVE1M16ALL | 1.7-1.95V | 70 | TFBGA[48] | Production | Asynch/Page |
| | 1MX16 | IS66WVE1M16DBLL | 2.7-3.6V | 55,70 | TFBGA[48] | Production | Asynch/Page |
| 32M | 1MX16 | IS66WVC1M16ALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 1.5 |
| | 1MX16 | IS66WVD1M16ALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 2.0 |
| | 2MX16 | IS66WVE2M16ALL | 1.7-1.95V | 70 | TFBGA[48] | Production | Asynch/Page |
| | 2MX16 | IS66WVE2M16DBLL | 2.7-3.6V | 70 | TFBGA[48] | Production | Asynch/Page |
| 64M | 2MX16 | IS66WVC2M16ALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 1.5 |
| | 2MX16 | IS66WVD2M16DALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 2.0 |
| | 4MX16 | IS66WVE4M16ALL | 1.7-1.95V | 70 | TFBGA[48] | Production | Asynch/Page |
| | 4MX16 | IS66WVE4M16BLL | 2.7-3.6V | 70 | TFBGA[48] | Production | Asynch/Page |
| 64M | 4MX16 | IS66WVc4M16ALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 1.5 |
| | 4MX16 | IS66WVD4M16ALL | 1.7-1.95V | 70 | VFBGA[54] | Production | CRAM 2.0 |

CellularRAM™ is a registered trademark of CellularRAM



ADVANCED MEMORY SOLUTIONS
INNOVATIVE ANALOG AND MIXED SIGNAL SOLUTIONS

Pseudo SRAM/CellularRAM™



Functional Block Diagram of IS66WVD4M16ALL

ISSI PSRAM/CellularRAM™ is compatible with Micron

| ISSI Part Number | Micron Part Number | Density |
|-------------------------|------------------------|---------|
| IS66WVC1M16ALL-7010BLI | MT45W1MW16BDGB-701 IT | 16Mb |
| IS66WVC1M16ALL-7008BLI | MT45W1MW16BDGB-708 AT | 16Mb |
| IS66WVE1M16ALL-70BLI | MT45W1MW16PDGA-70 IT | 16Mb |
| IS66WVC2M16DALL-7010BLI | MT45W2MW16BGB-701 IT | 32Mb |
| IS66WVE2M16DALL-70BLI | MT45W2MW16PGA-70 IT | 32Mb |
| IS66WVC4M16ALL-7010BLI | MT45W4MW16BCGB-701 IT | 64Mb |
| IS66WVE4M16ALL-70BLI | MT45W4MW16PCGA-70 IT | 64Mb |
| IS66WVE4M16ALL-70BLI | MT45W4MW16PCGA-70 L WT | 64Mb |

ISSI is committed to provide our customers with long term product support. ISSI has long known to be the supplier for product longevity and we continue to excel in this area. Our products are designed with the best fit latest process technology for better lead time and availability. In addition, our quality and reliability will meet all stringent requirements of different applications.

For more information or questions, please contact: SRAM@issi.com

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